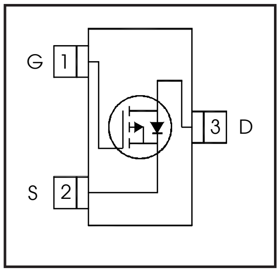
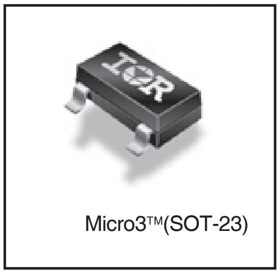
International
IOR Rectifier

IRLML6402PbF-1

HEXFET® Power MOSFET

V_{DS}	-20	V
$R_{DS(on)}$ max (@V_{GS} = -4.5V)	0.065	Ω
$Q_{g\ (typical)}$	8.0	nC
I_D (@T_A = 25°C)	-3.7	A




Micro3™(SOT-23)

Features		Benefits
Industry-standard pinout SOT-23 Package	⇒	Multi-Vendor Compatibility
Compatible with Existing Surface Mount Techniques		Easier Manufacturing
RoHS Compliant, Halogen-Free		Environmentally Friendlier
MSL1, Industrial qualification		Increased Reliability

Base Part Number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
IRLML6402TRPbF-1	Micro3™ (SOT-23)	Tape and Reel	3000	IRLML6402TRPbF-1

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{DS}	Drain- Source Voltage	-20	V
I_D @ T_A = 25°C	Continuous Drain Current, V_{GS} @ -4.5V	-3.7	A
I_D @ T_A= 70°C	Continuous Drain Current, V_{GS} @ -4.5V	-2.2	
I_{DM}	Pulsed Drain Current ①	-22	
P_D @T_A = 25°C	Power Dissipation	1.3	W
P_D @T_A = 70°C	Power Dissipation	0.8	
	Linear Derating Factor	0.01	W/°C
E_{AS}	Single Pulse Avalanche Energy④	11	mJ
V_{GS}	Gate-to-Source Voltage	± 12	V
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to + 150	°C

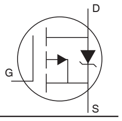
Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Maximum Junction-to-Ambient③	75	100	°C/W

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	-20	—	—	V	V_{GS} = 0V, I_D = -250μA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	-0.009	—	V/°C	Reference to 25°C, I_D = -1mA ②
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	0.050	0.065	Ω	V_{GS} = -4.5V, I_D = -3.7A ②
		—	0.080	0.135		V_{GS} = -2.5V, I_D = -3.1A ②
$V_{GS(th)}$	Gate Threshold Voltage	-0.40	-0.55	-1.2	V	V_{DS} = V_{GS}, I_D = -250μA
g_{fs}	Forward Transconductance	6.0	—	—	S	V_{DS} = -10V, I_D = -3.7A ②
I_{DSS}	Drain-to-Source Leakage Current	—	—	-1.0	μA	V_{DS} = -20V, V_{GS} = 0V
		—	—	-25		V_{DS} = -20V, V_{GS} = 0V, T_J = 70°C
I_{GSS}	Gate-to-Source Forward Leakage	—	—	-100	nA	V_{GS} = -12V
	Gate-to-Source Reverse Leakage	—	—	100		V_{GS} = 12V
Q_g	Total Gate Charge	—	8.0	12	nC	I_D = -3.7A
Q_{gs}	Gate-to-Source Charge	—	1.2	1.8		V_{DS} = -10V
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	2.8	4.2		V_{GS} = -5.0V ②
$t_{d(on)}$	Turn-On Delay Time	—	350	—	ns	V_{DD} = -10V
t_r	Rise Time	—	48	—		I_D = -3.7A
$t_{d(off)}$	Turn-Off Delay Time	—	588	—		R_G = 89Ω
t_f	Fall Time	—	381	—		R_D = 2.7Ω
C_{iss}	Input Capacitance	—	633	—	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	—	145	—		V_{DS} = -10V
C_{rss}	Reverse Transfer Capacitance	—	110	—		f = 1.0MHz

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	-1.3	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	-22		
V_{SD}	Diode Forward Voltage	—	—	-1.2	V	T_J = 25°C, I_S = -1.0A, V_{GS} = 0V ②
t_{rr}	Reverse Recovery Time	—	29	43	ns	T_J = 25°C, I_F = -1.0A
Q_{rr}	Reverse RecoveryCharge	—	11	17	nC	di/dt = -100A/μs ②

Notes:

① Repetitive rating; pulse width limited by max. junction temperature.

② Pulse width ≤ 400μs; duty cycle ≤ 2%.

③ Surface mounted on 1" square single layer 1oz. copper FR4 board, steady state.

④ Starting T_J = 25°C, L = 1.65mH R_G = 25Ω, I_{AS} = -3.7A.

** For recommended footprint and soldering techniques refer to application note #AN-994.

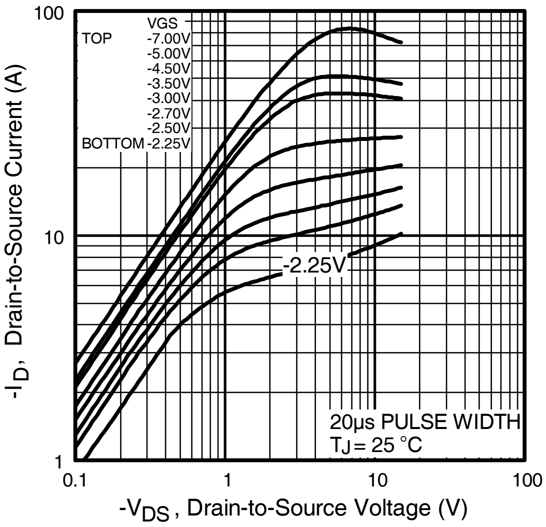


Fig 1. Typical Output Characteristics

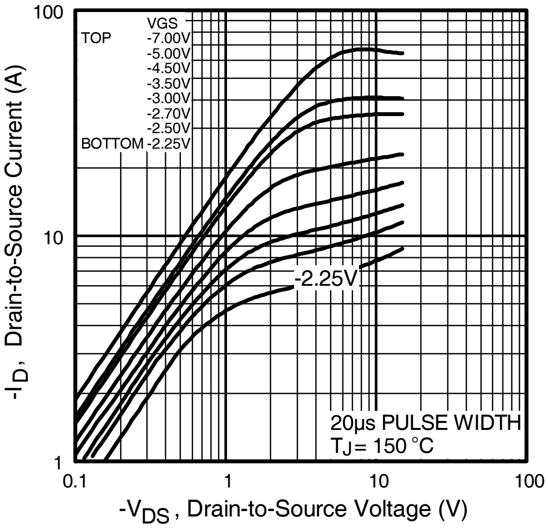


Fig 2. Typical Output Characteristics

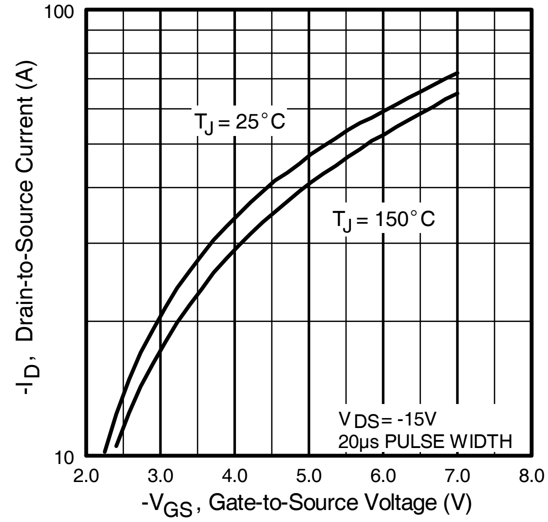


Fig 3. Typical Transfer Characteristics

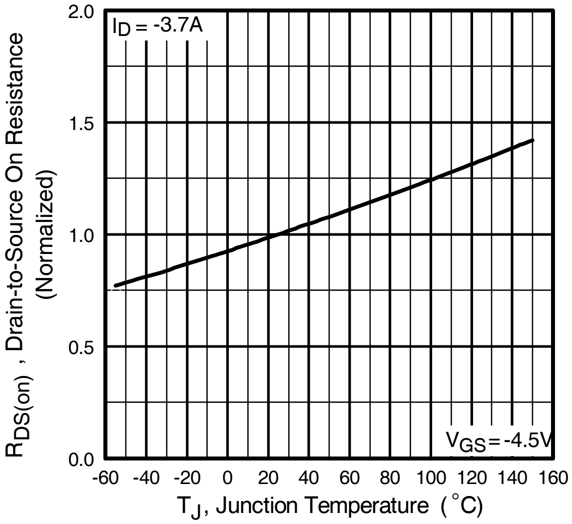


Fig 4. Normalized On-Resistance
Vs. Temperature

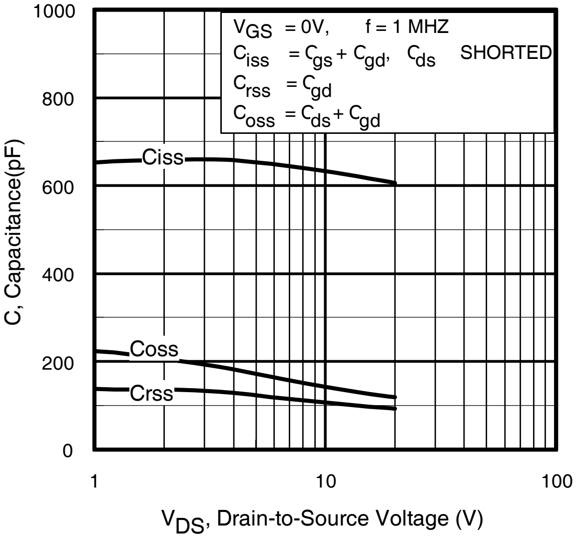


Fig 5. Typical Capacitance Vs.
Drain-to-Source Voltage

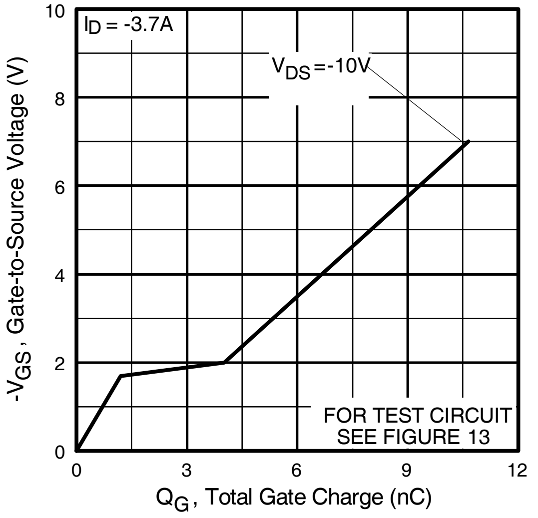


Fig 6. Typical Gate Charge Vs.
Gate-to-Source Voltage

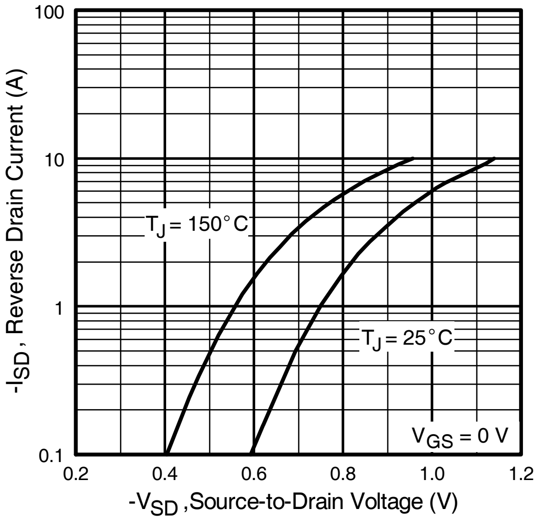


Fig 7. Typical Source-Drain Diode
Forward Voltage

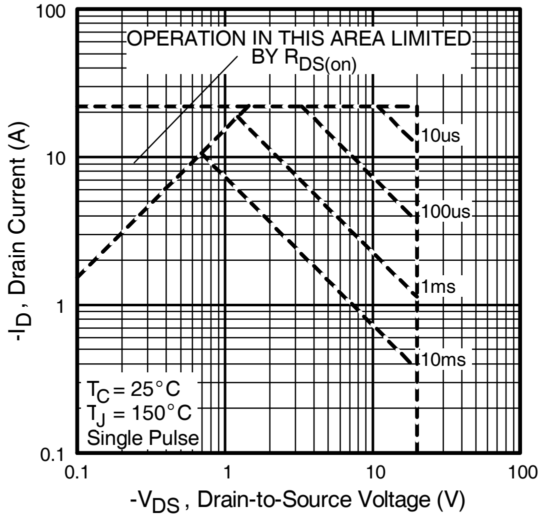


Fig 8. Maximum Safe Operating Area

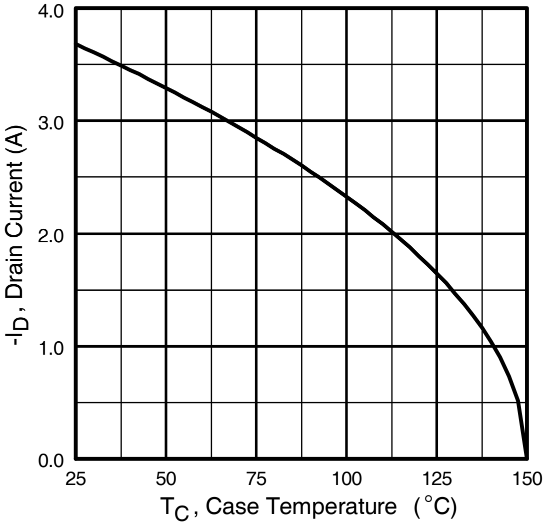


Fig 9. Maximum Drain Current Vs. Case Temperature

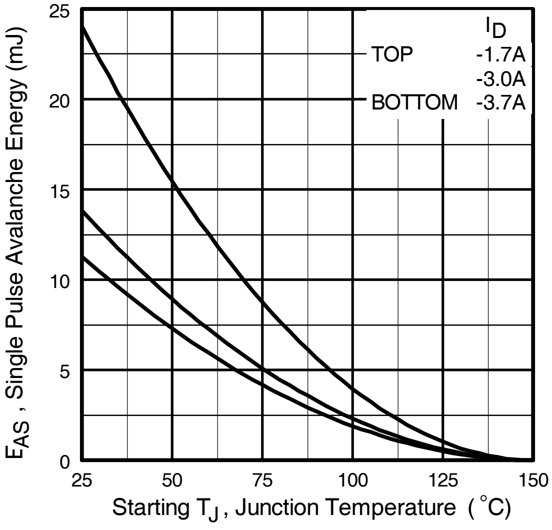


Fig 10. Maximum Avalanche Energy Vs. Drain Current

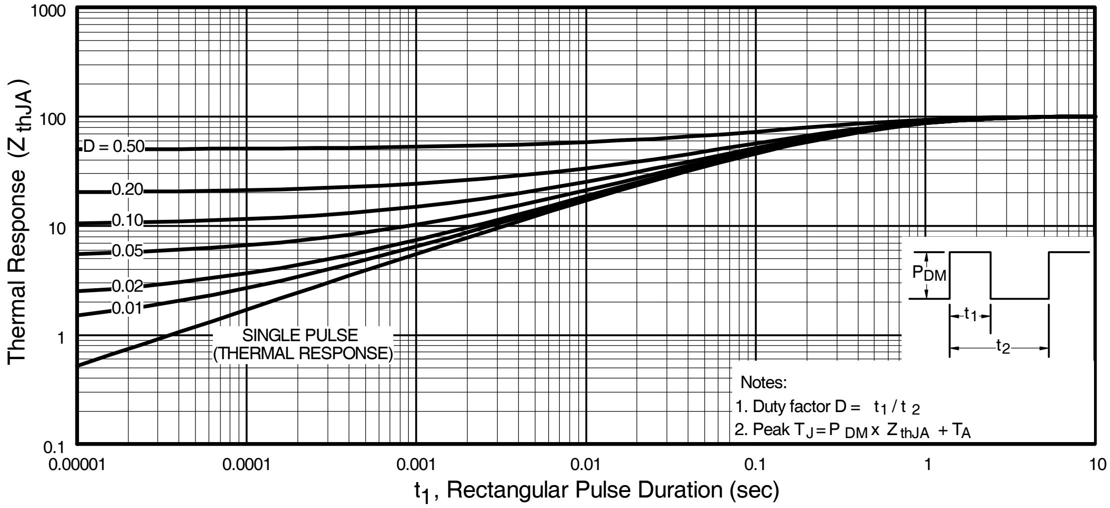


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

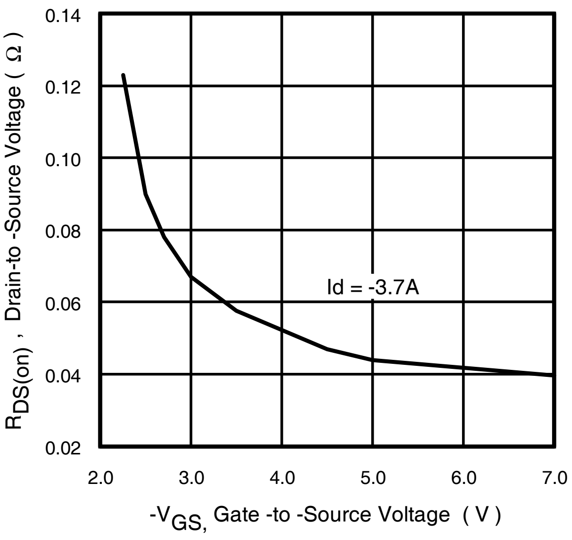


Fig 12. Typical On-Resistance Vs. Gate Voltage

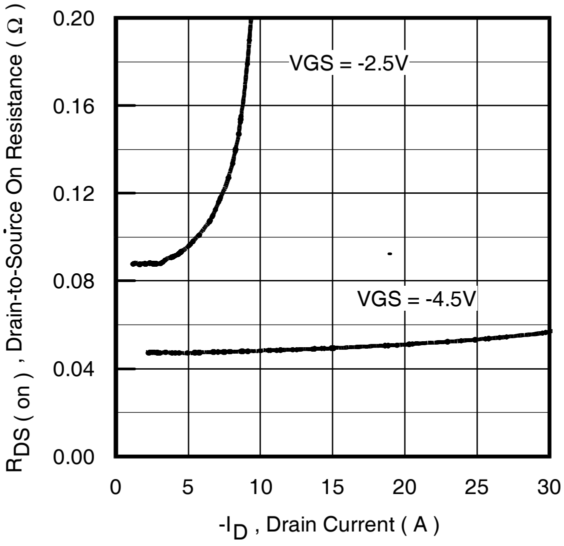
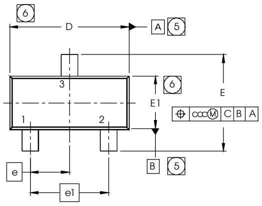


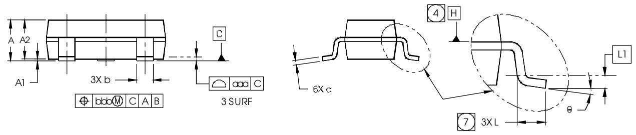
Fig 13. Typical On-Resistance Vs. Drain Current

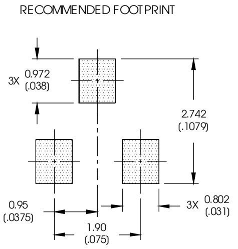
Micro3 (SOT-23) (Lead-Free) Package Outline

Dimensions are shown in millimeters (inches)



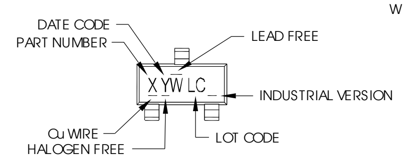
SYMBOL	DIMENSIONS			
	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.89	1.12	.036	.044
A1	0.01	0.10	.0004	.0039
A2	0.88	1.02	.035	.040
b	0.30	0.50	.0119	.0196
c	0.08	0.20	.0032	.0078
D	2.80	3.04	.111	.119
E	2.10	2.64	.083	.103
E1	1.20	1.40	.048	.055
e	0.95 BSC		.0375 BSC	
e1	1.90 BSC		.075 BSC	
L	0.40	0.60	.0158	.0236
L1	0.25 BSC		.0118 BSC	
θ	0°	8°	0°	8°
aaa	0.10		.004	
bbb	0.20		.008	
ccc	0.15		.006	





NOTES
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
2. DIMENSIONS ARE SHOWN IN MILLIMETERS AND INCHES.
3. CONTROLLING DIMENSION: MILLIMETER.
4. DATUM PLANE H IS LOCATED AT THE MOLD PARTING LINE.
5. DATUM A AND B TO BE DETERMINED AT DATUM PLANE H.
6. DIMENSIONS D AND E1 ARE MEASURED AT DATUM PLANE H.
7. DIMENSION L IS THE LEAD LENGTH FOR SOLDERING TO A SUBSTRATE.
8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-236AB.

Micro3 (SOT-23 / TO-236AB) Part Marking Information



X = PART NUMBER CODE REFERENCE:

A = IRLML2402
B = IRLML2803
C = IRLML6302
D = IRLML5103
E = IRLML6402
F = IRLML6401
G = IRLML2502
H = IRLML5203
I = IRLML0030
J = IRLML2030
K = IRLML0100
L = IRLML0060
M = IRLML0040
N = IRLML2060
P = IRLML9301
R = IRLML9303

S = IRLML6244
T = IRLML6246
U = IRLML6344
V = IRLML6346
W = IRFML8244
X = IRLML2244
Y = IRLML2246
Z = IRFML9244

Note: A line above the work week (as shown here) indicates Lead - Free.

W = (1-26) IF PRECEDED BY LAST DIGIT OF CALENDAR YEAR

YEAR		Y	WORK WEEK	W
2011	2001	1	01	A
2012	2002	2	02	B
2013	2003	3	03	C
2014	2004	4	04	D
2015	2005	5		
2016	2006	6		
2017	2007	7	↓	↓
2018	2008	8		
2019	2009	9		
2020	2010	0	24	X
			25	Y
			26	Z

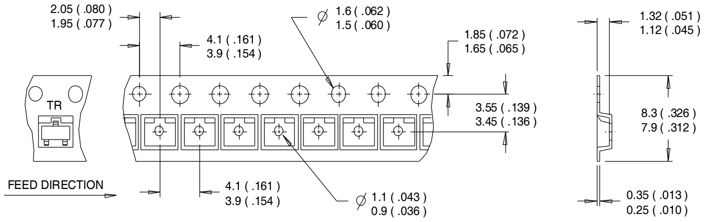
W = (27-52) IF PRECEDED BY A LETTER

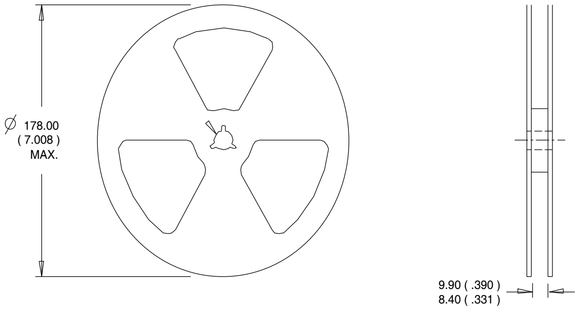
YEAR		Y	WORK WEEK	W
2011	2001	A	27	A
2012	2002	B	28	B
2013	2003	C	29	C
2014	2004	D	30	D
2015	2005	E		
2016	2006	F		
2017	2007	G	↓	↓
2018	2008	H		
2019	2009	J		
2020	2010	K	50	X
			51	Y
			52	Z

Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

Micro3™(SOT-23/TO-263AB) Tape & Reel Information

Dimensions are shown in millimeters (inches)





NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

Qualification information†

Qualification level	Industrial (per JEDEC JESD47F †† guidelines)	
Moisture Sensitivity Level	Micro3™ (SOT-23)	MSL1 (per JEDEC J-STD-020D††)
RoHS compliant	Yes	

† Qualification standards can be found at International Rectifier's web site: http://www.irf.com/product-info/reliability
†† Applicable version of JEDEC standard at the time of product release

Revision History

Date	Comment
10/28/2014	• Updated partmarking to reflect Industrial partmarking on page 7.

International
Rectifier

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